

Список основных публикаций С.Ю. Турищев по смежным оппонируемой диссертации тематикам в рецензируемых изданиях за последние 5 лет

1. Antipov S. S., Pichkur E. B., Praslova N. V., Preobrazhenskaya E. V., Usoltseva D. S., Belikov E. A., Chuvenkova O. A., Presnyakov M. Y., Artyukhov V. G., Ozoline O. N., Turishchev S. Y. High resolution cryogenic transmission electron microscopy study of *Escherichia coli* Dps protein: First direct observation in quasinative state // Results in Physics. – 2018. – T. 11. – C. 926-928.
2. Chuvenkova O. A., Domashevskaya E. P., Ryabtsev S. V., Yurakov Y. A., Popov A. E., Koyuda D. A., Nesterov D. N., Spirin D. E., Ovsyannikov R. Y., Turishchev S. Y. XANES and XPS investigations of surface defects in wire-like SnO₂ crystals // Physics of the Solid State. – 2015. – T. 57, № 1. – C. 153-161.
3. Domashevskaya E. P., Chuvenkova O. A., Turishchev S. Y. Synchrotron characterization of functional tin dioxide nanowires // AIP Conference Proceedings. – 2015. – T. 1697, № 1.
4. Domashevskaya E. P., Terekhov V. A., Turishchev S. Y., Prijimov A. S., Kharin A. N., Parinova E. V., Rumyantseva N. A., Usoltseva D. S., Fomenko Y. L., Belenko S. V. Atomic and electronic structure of amorphous and nanocrystalline layers of semi-insulating silicon produced by chemical-vapor deposition at low pressures // Journal of Surface Investigation. X-ray, Synchrotron and Neutron Techniques. – 2015. – T. 9, № 6. – C. 1228-1236.
5. Manyakin M. D., Kurganskii S. I., Dubrovskii O. I., Chuvenkova O. A., Domashevskaya E. P., Ryabtsev S. V., Ovsyannikov R., Parinova E. V., Sivakov V., Turishchev S. Y. Electronic and atomic structure studies of tin oxide layers using X-ray absorption near edge structure spectroscopy data modelling // Materials Science in Semiconductor Processing. – 2019. – T. 99. – C. 28-33.
6. Manyakin M. D., Kurganskii S. I., Dubrovskii O. I., Chuvenkova O. A., Domashevskaya E. P., Ryabtsev S. V., Ovsyannikov R., Turishchev S. Y. A novel approach to the electronic structure and surface composition investigations of tin-oxygen system materials by means of X-ray absorption spectroscopy combined with ab initio calculations // Computational Materials Science. – 2016. – T. 121. – C. 119-123.
7. Shaposhnik A. V., Shaposhnik D. A., Turishchev S. Y., Chuvenkova O. A., Ryabtsev S. V., Vasiliev A. A., Vilanova X., Hernandez-Ramirez F., Morante J. R. Gas sensing properties of individual SnO₂ nanowires and SnO₂ sol-gel nanocomposites // Beilstein Journal of Nanotechnology. – 2019. – T. 10. – C. 1380-1390.
8. Terekhov V. A., Lazaruk S. K., Usol'tseva D. S., Leshok A. A., Katsuba P. S., Zanin I. E., Spirin D. E., Stepanova A. A., Turishchev S. Y. Specific features of the electronic and atomic structures of silicon single crystals in the aluminum matrix // Physics of the Solid State. – 2014. – T. 56, № 12. – C. 2543-2547.
9. Terekhov V. A., Nesterov D. N., Domashevskaya E. P., Geraskina E. V., Manyakin M. D., Kurganskii S. I., Kamayev G. N., Antonenko A. H., Turishchev S. Y. The electronic structure peculiarities of a strained silicon layer in silicon-on-insulator:

Experimental and theoretical data // Applied Surface Science. – 2016. – T. 382. – C. 331-335.

10. Turishchev S. Y., Chuvenkova O. A., Parinova E. V., Koyuda D. A., Chumakov R. G., Presselt M., Schleusener A., Sivakov V. XPS investigations of MOCVD tin oxide thin layers on Si nanowires array // Results in Physics. – 2018. – T. 11. – C. 507-509.
11. Turishchev S. Y., Parinova E. V., Nesterov D. N., Koyuda D. A., Sivakov V., Schleusener A., Terekhov V. A. Synchrotron studies of top-down grown silicon nanowires // Results in Physics. – 2018. – T. 9. – C. 1494-1496.
12. Turishchev S. Y., Parinova E. V., Pisliaruk A. K., Koyuda D. A., Yermukhamed D., Ming T., Ovsyannikov R., Smirnov D., Makarova A., Sivakov V. Surface deep profile synchrotron studies of mechanically modified top-down silicon nanowires array using ultrasoft X-ray absorption near edge structure spectroscopy // Scientific Reports. – 2019. – T. 9, № 1. – C. 8066.
13. Turishchev S. Y., Terekhov V. A., Koyuda D. A., Ershov A. V., Mashin A. I., Parinova E. V., Nesterov D. N., Grachev D. A., Karabanova I. A., Domashevskaya E. P. Formation of silicon nanocrystals in multilayer nanoperiodic a-SiO_x/insulator structures from the results of synchrotron investigations // Semiconductors. – 2017. – T. 51, № 3. – C. 349-352.
14. Turishchev S. Y., Terekhov V. A., Nesterov D. N., Koltygina K. G., Sivakov V. A., Domashevskaya E. P. Atomic and electronic structure peculiarities of silicon wires formed on substrates with varied resistivity according to ultrasoft X-ray emission spectroscopy // Technical Physics Letters. – 2015. – T. 41, № 4. – C. 344-347.